

## Silicon NPN Power Transistors

## 2SC1226 2SC1226A

## DESCRIPTION

- With TO-202 package
- Complement to type 2SA699/699A

## APPLICATIONS

- For medium power amplifier applications

## PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

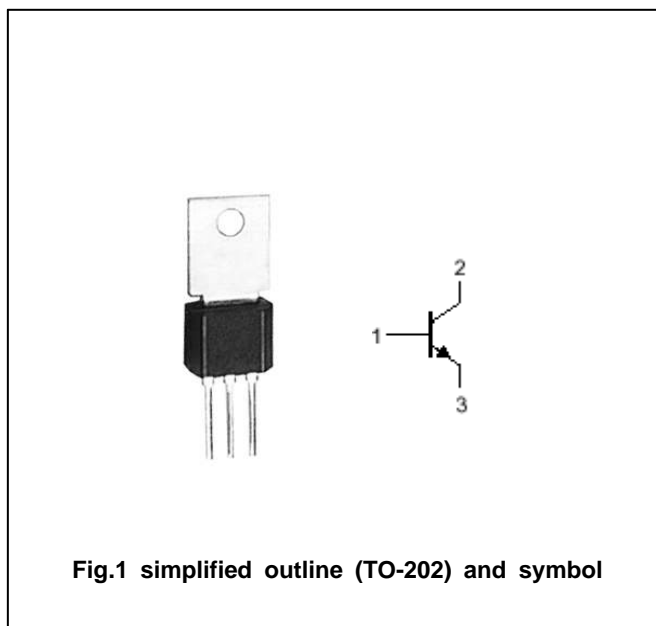


Fig.1 simplified outline (TO-202) and symbol

## Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	2SC1226	40	V
		2SC1226A	50	
V <sub>CEO</sub>	Collector-emitter voltage	2SC1226	32	V
		2SC1226A	40	
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		2	A
I <sub>CM</sub>	Collector current-peak		3	A
I <sub>B</sub>	Base current		0.6	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	10	W
T <sub>J</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =2A ; I <sub>B</sub> =0.2 A		0.4	1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =2A ; I <sub>B</sub> =0.2 A			1.5	V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =1mA; I <sub>E</sub> =0	2SC1226	40		V
			2SC1226A	50		
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =10mA; I <sub>B</sub> =0	2SC1226	32		V
			2SC1226A	40		
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =20V; I <sub>E</sub> =0			1	μ A
I <sub>CEO</sub>	Collector cut-off current	V <sub>CE</sub> =12V; I <sub>B</sub> =0			100	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			100	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V	50		220	
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =5V; f=1MHz		50		pF
f <sub>T</sub>	Transition frequency	I <sub>E</sub> =0.5A ; V <sub>CB</sub> =5V		150		MHz

◆ h<sub>FE</sub> classifications

P	Q	R
50-100	80-160	100-220

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PACKAGE OUTLINE

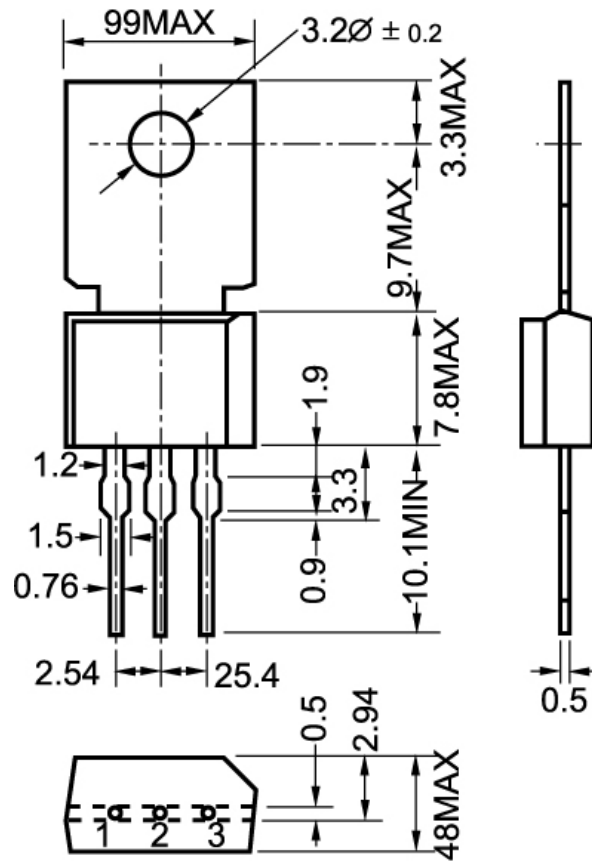


Fig.2 outline dimensions

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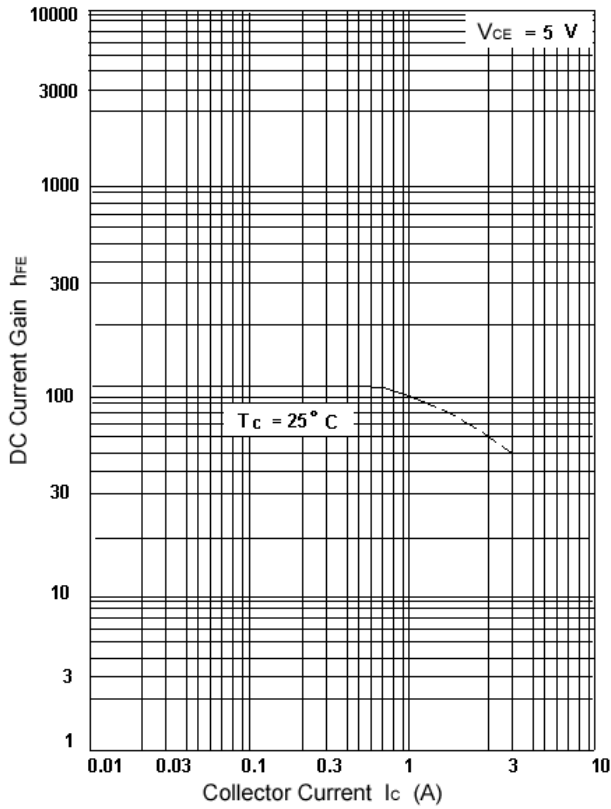


Fig.3 DC current Gain

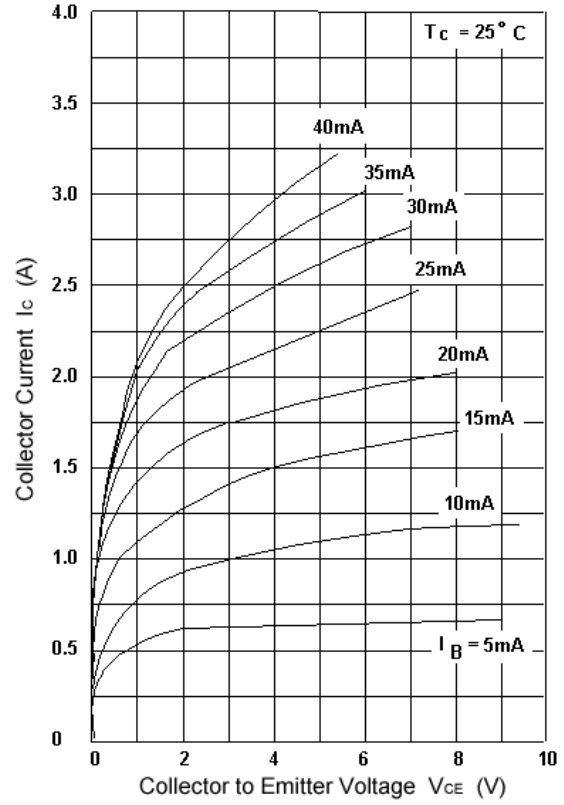


Fig.4 Static Characteristic

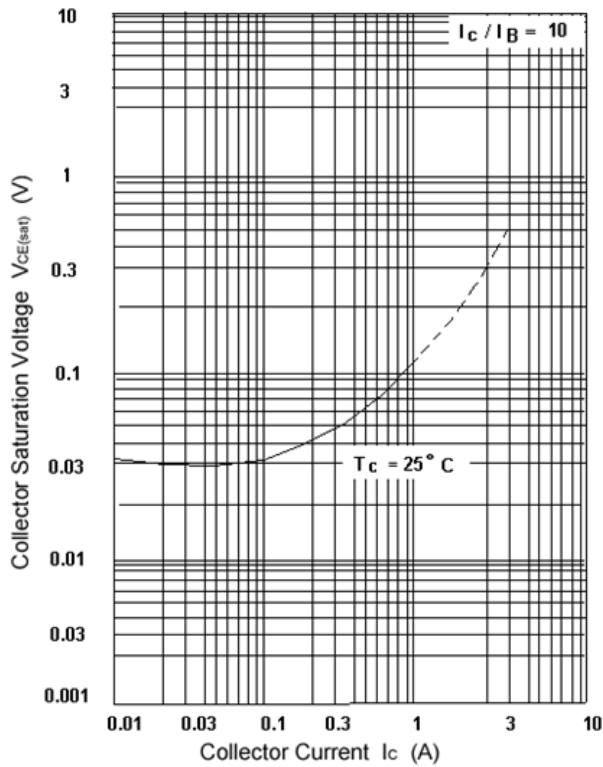


Fig.5 Collector-Emitter Saturation Voltage

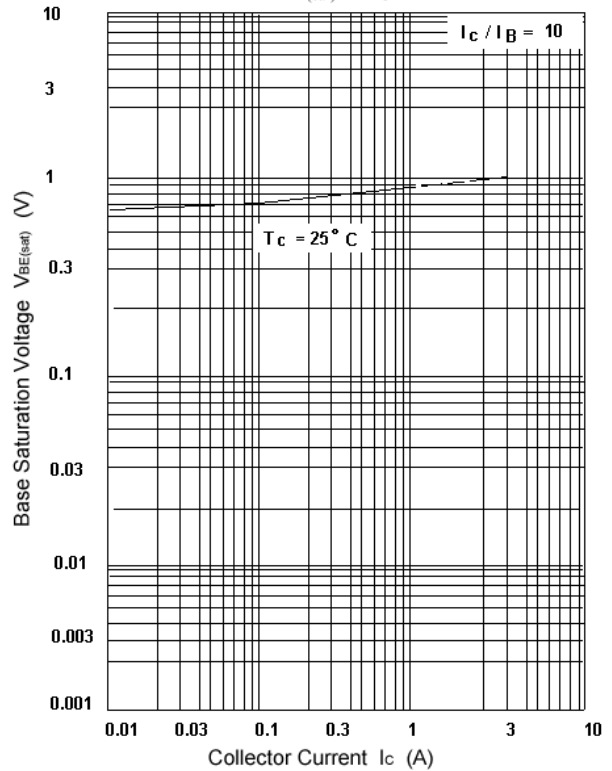


Fig.6 Base-Emitter Saturation Voltage

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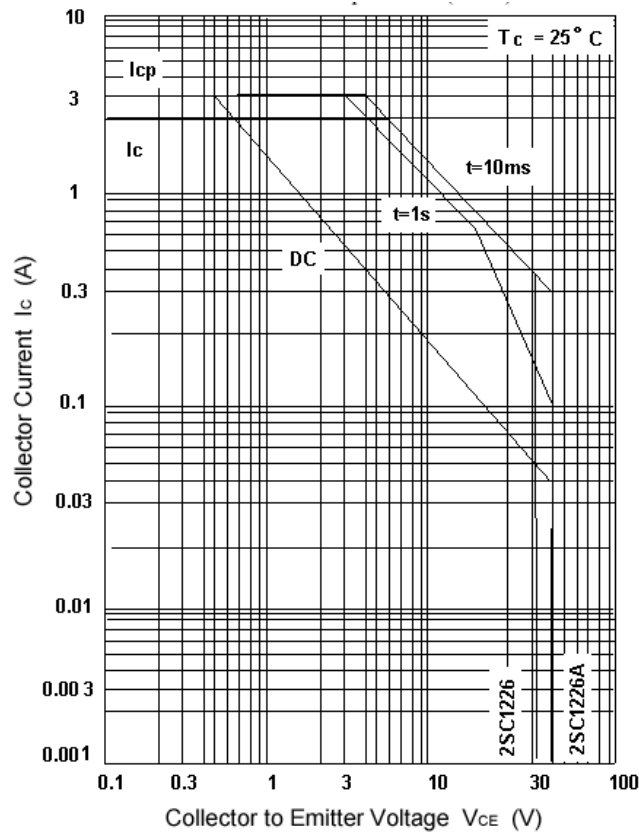


Fig.7 Safe Operating Area